

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	6849	IGBT or "insulated gate bipolar transistor"	USPAT; EPO; JPO; Derwent; IBM TDB	2000/11/30 18:41	
2	BRS	L2	3090	diode and 1	USPAT; EPO; JPO; Derwent; IBM TDB	2000/11/30 20:37	